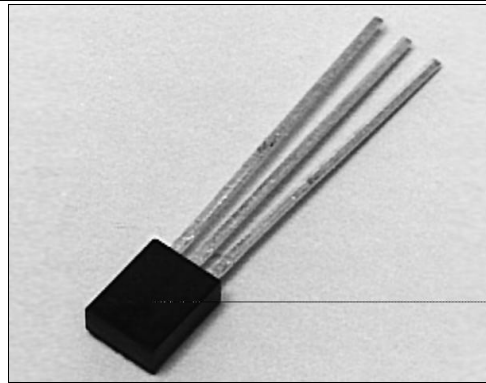


# HLC1395

## Reflective Sensor

### FEATURES

- Side-looking plastic package
- Phototransistor output
- IR emitter and phototransistor detector in a single package
- Low profile for design flexibility
- Designed for short distance detection
- High sensitivity
- Unfocused for sensing diffused surfaces



INFRA-58.TIF

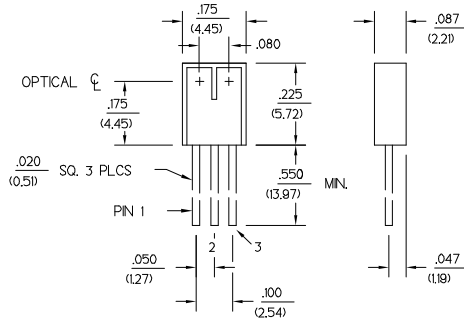
### DESCRIPTION

The HLC1395 is a miniature infrared sensor designed to sense reflective objects at short distances. Both the GaAs IRED and the NPN phototransistor are mounted side-by-side in a single black plastic package with an integral barrier to minimize crosstalk. The sensor is configured with the IRED cathode and the phototransistor emitter connected to a common lead.

The housing consists of an opaque polysulfone outer shell with transfer-molded, IR-transmissive epoxy encapsulant. Housings are soluble in chlorinated hydrocarbons and ketones. Recommended cleaning agents are methanol and isopropanol.

### OUTLINE DIMENSIONS in inches (mm)

Tolerance 3 plc decimals  $\pm 0.010(0.25)$   
2 plc decimals  $\pm 0.030(0.76)$



DIM\_029.cdr

# HLC1395

Reflective Sensor

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)						
PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
<b>IR EMITTER</b>						
Forward Voltage	V <sub>F</sub>			1.6	V	I <sub>F</sub> =20 mA
Reverse Current	I <sub>R</sub>			10	μA	V <sub>R</sub> =3 V
<b>DETECTOR</b>						
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	30			V	I <sub>C</sub> =100 μA
Emitter-Collector Breakdown Voltage	V <sub>(BR)ECO</sub>	5.0			V	I <sub>E</sub> =100 μA
Collector Dark Current	I <sub>CDO</sub>			100	nA	V <sub>CE</sub> =10 V, I <sub>F</sub> =0
<b>COUPLED CHARACTERISTICS</b>						
On-State Collector Current	I <sub>C(ON)</sub>				mA	V <sub>CE</sub> =5 V
HLC1395-001		0.30				I <sub>F</sub> =10 mA
HLC1395-002		0.60				(1)
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		0.5		V	I <sub>C</sub> =40 μA, I <sub>F</sub> =10 mA (1)
Crosstalk (2)	I <sub>CX</sub>		15		μA	V <sub>CE</sub> =5 V, I <sub>F</sub> =10 mA
Rise And Fall Time	t <sub>r</sub> , t <sub>f</sub>		15		μs	V <sub>CC</sub> =5 V, I <sub>C</sub> =0.3 mA R <sub>L</sub> =1000 Ω

Notes  
1. Test surface is Eastman Kodak neutral white test card with 90% diffuse reflectance located 0.040 in. (1.0 mm) from the front surface of the device.  
2. Crosstalk (I<sub>CX</sub>) is the collector current measured with current to emitter and no reflecting surface.

## ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

Operating Temperature Range -40°C to 85°C  
Storage Temperature Range -40°C to 85°C  
Soldering Temperature (5 sec) 240°C

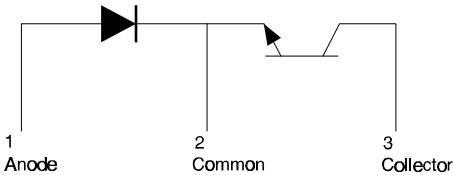
### IR EMITTER

Reverse Voltage 3 V  
Continuous Forward Current 50 mA  
Power Dissipation 100 mW (1)

### DETECTOR

Collector-Emitter Voltage 30 V  
Emitter-Collector Voltage 5 V  
Power Dissipation 100 mW (1)  
Collector DC Current 30 mA

## SCHEMATIC



Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

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# HLC1395

## Reflective Sensor

Fig. 1 Normalized Light Current ( $I_L$ ) vs Distance to Reflective Surface

gra\_071.ds4

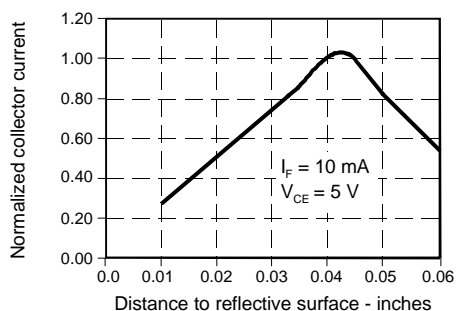


Fig. 2 Normalized Light Current ( $I_L$ ) vs IRED Forward Current

gra\_072.ds4

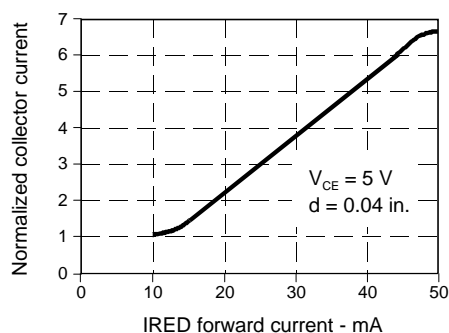


Fig. 3 IRED Forward Bias Characteristics

gra\_073.ds4

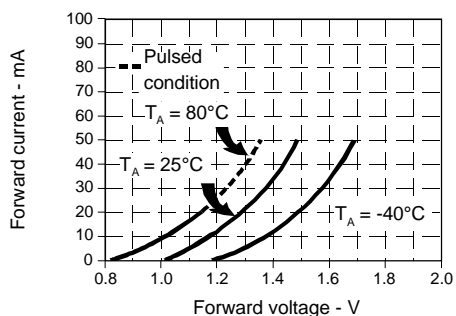


Fig. 4 Non-Saturated Switching Time vs Load Resistance

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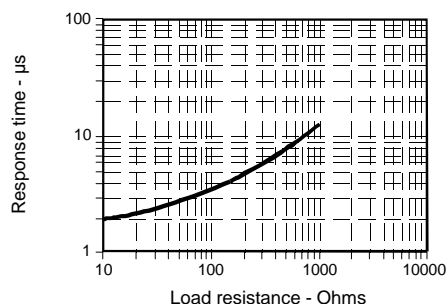


Fig. 5 Dark Current vs Temperature

gra\_301.cdr

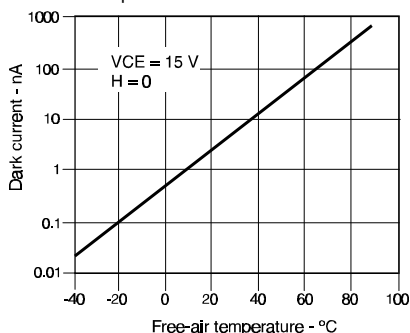
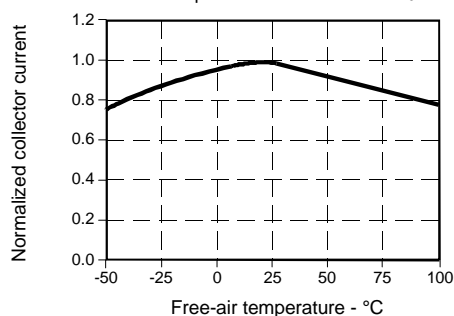


Fig. 6 Collector Current vs Ambient Temperature

gra\_076.ds4



All Performance Curves Show Typical Values

# HLC1395

Reflective Sensor

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